

BUK7619-100B

N-channel TrenchMOS standard level FET

Rev. 01 — 10 October 2007

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode power Field-Effect Transistor (FET) in a plastic package using NXP High Performance Automotive (HPA) TrenchMOS technology.

1.2 Features

- TrenchMOS technology
- 175 °C rated
- Q101 compliant
- Standard level compatible

1.3 Applications

- Automotive systems
- Motors, lamps and solenoids
- General purpose power switching
- 12 V, 24 V and 42 V loads.

1.4 Quick reference data

- $E_{DS(AL)S} \leq 222$ mJ
- $I_D \leq 64$ A
- $R_{DSon} = 17$ m Ω (typ)
- $P_{tot} \leq 200$ W

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	gate (G)	<p>SOT404 (D2PAK)</p>	<p>mbb076</p>
2	drain (D)		
3	source (S)		
mb	mounting base; connected to drain (D)		

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BUK7619-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3-leads (one lead cropped)	SOT404

4. Limiting values

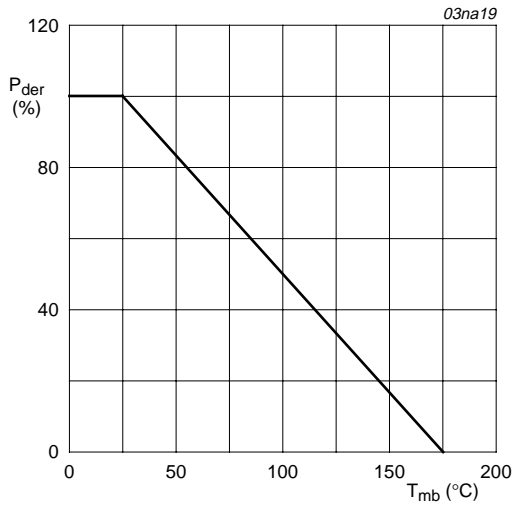
Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	100	V
V_{DGR}	drain-gate voltage (DC)	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-	± 20	V
I_D	drain current	$T_{sp} = 25 \text{ }^\circ\text{C}$; $V_{GS} = 10 \text{ V}$; see Figure 2 and 3	-	64	A
		$T_{sp} = 100 \text{ }^\circ\text{C}$; $V_{GS} = 10 \text{ V}$; see Figure 2	-	45	A
I_{DM}	peak drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$; see Figure 3	-	256	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$; see Figure 1	-	200	W
T_{stg}	storage temperature		-55	+175	$^\circ\text{C}$
T_j	junction temperature		-55	+175	$^\circ\text{C}$
Source-drain diode					
I_{DR}	reverse drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	64	A
I_{DRM}	peak reverse drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$	-	256	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 64 \text{ A}$; $V_{DS} \leq 100 \text{ V}$; $R_{GS} = 50 \text{ }\Omega$; $V_{GS} = 10 \text{ V}$; starting at $T_j = 25 \text{ }^\circ\text{C}$	-	222	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[1]	-	mJ

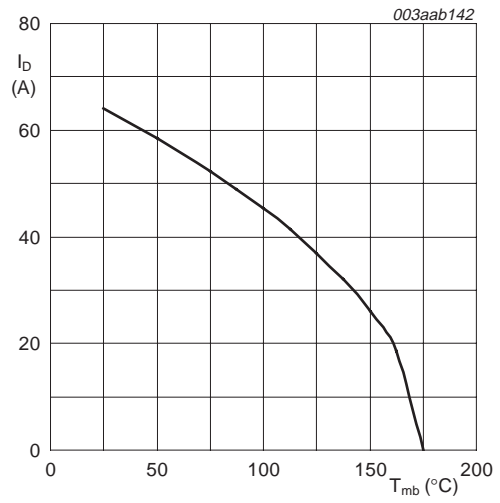
[1] Conditions:

- Maximum value not quoted. Repetitive rating defined in [Figure 16](#).
- Single-pulse avalanche rating limited by $T_{j(max)}$ of $175 \text{ }^\circ\text{C}$.
- Repetitive avalanche rating limited by an average junction temperature of $170 \text{ }^\circ\text{C}$.
- Refer to application note *AN10273* for further information.



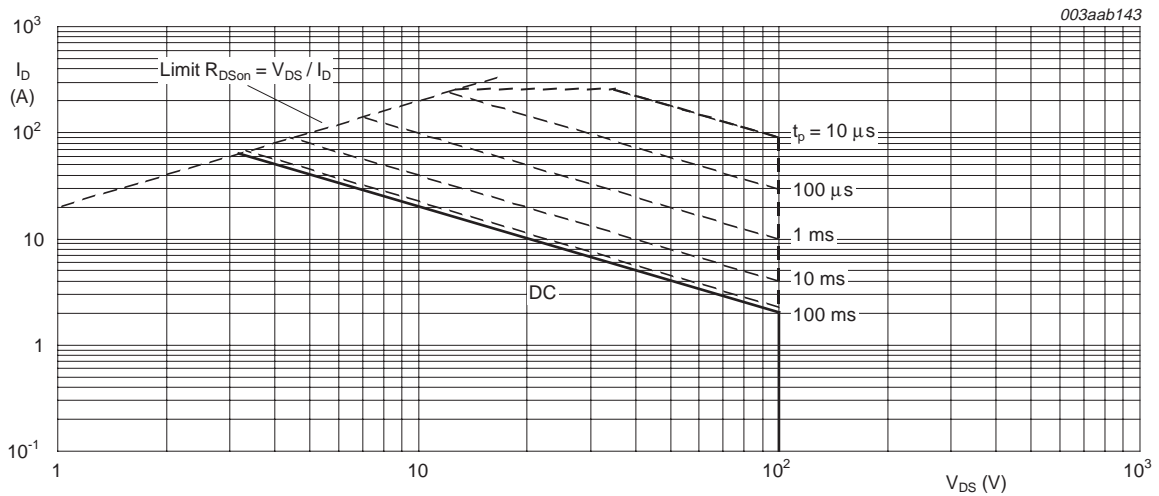
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10\text{ V}$

Fig 2. Continuous drain current as a function of mounting base temperature



$T_{mb} = 25^{\circ}C$; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.74	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W

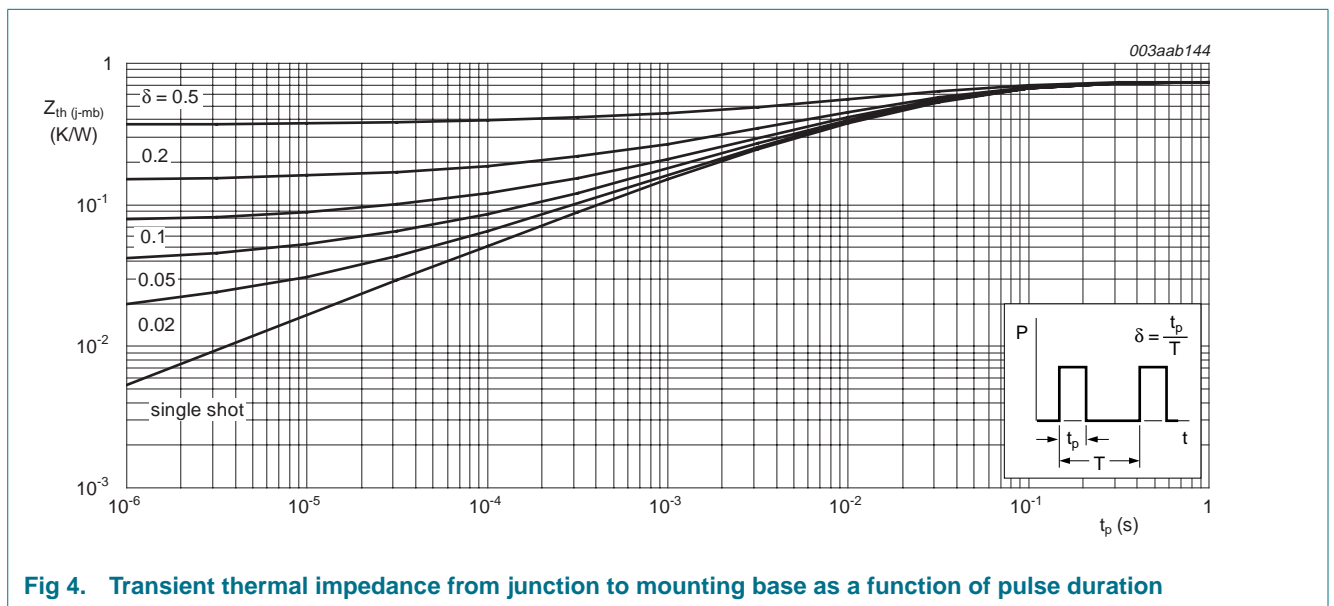
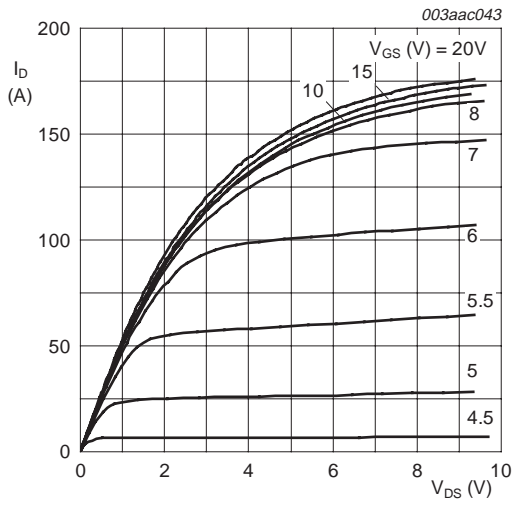


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

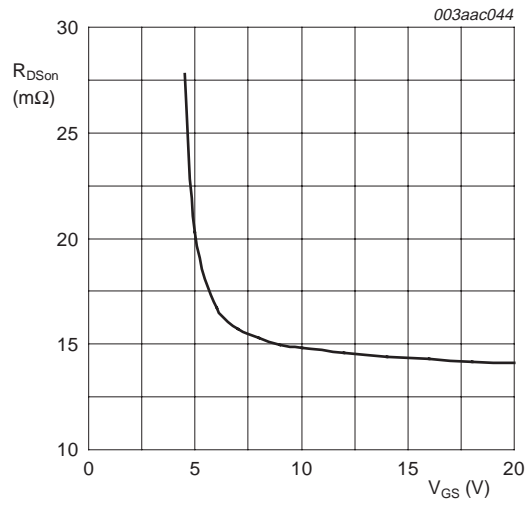
Table 5. Characteristics
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V				
		T _j = 25 °C	100	-	-	V
		T _j = -55 °C	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; see Figure 9 and 10				
		T _j = 25 °C	2	3	4	V
		T _j = 175 °C	1	-	-	V
		T _j = -55 °C	-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V				
		T _j = 25 °C	-	0.02	1	μA
		T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = ±20 V; V _{DS} = 0 V	-	2	100	nA
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; see Figure 7 and 8				
		T _j = 25 °C	-	17	19	mΩ
		T _j = 175 °C	-	-	49	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DD} = 80 V; V _{GS} = 10 V; see Figure 14	-	53	-	nC
Q _{GS}	gate-source charge		-	11	-	nC
Q _{GD}	gate-drain charge		-	27	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; see Figure 12	-	2555	3400	pF
C _{oss}	output capacitance		-	340	480	pF
C _{rss}	reverse transfer capacitance		-	84	115	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω;	-	19	-	ns
t _r	rise time	V _{GS} = 10 V; R _G = 10 Ω	-	45	-	ns
t _{d(off)}	turn-off delay time		-	85	-	ns
t _f	fall time		-	34	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; di _S /dt = -100 A/μs;	-	116	-	ns
Q _r	recovered charge	V _{GS} = 0 V; V _R = 30 V	-	130	-	nC



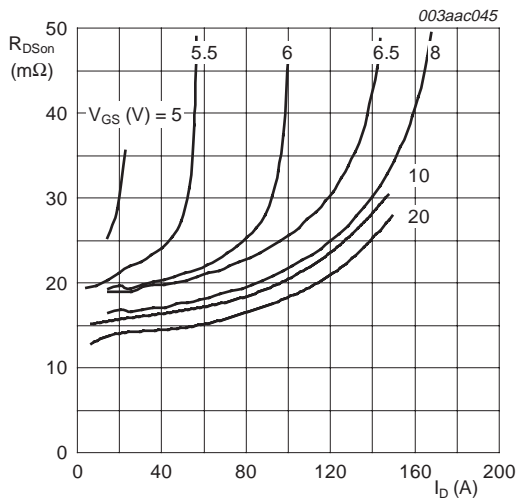
$T_j = 25\text{ °C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



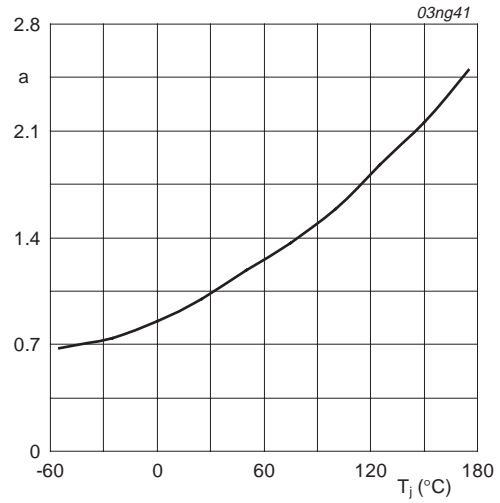
$T_j = 25\text{ °C}; I_D = 10\text{ A}$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



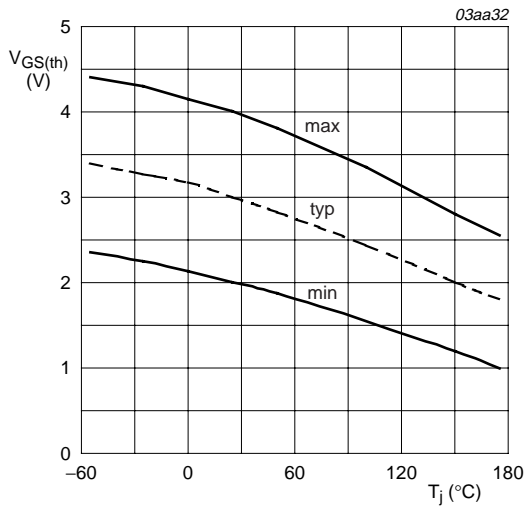
$T_j = 25\text{ °C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



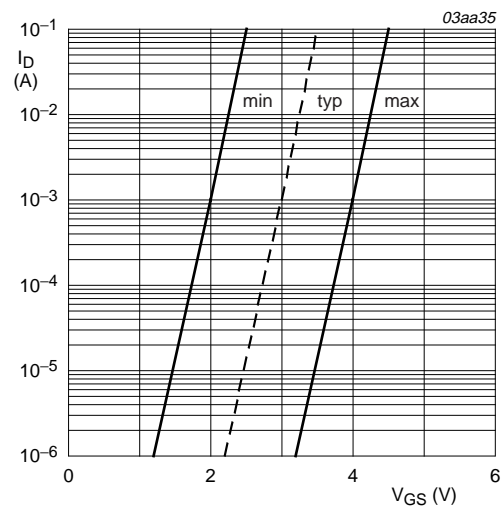
$$a = \frac{R_{DSon}}{R_{DSon(25\text{°C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



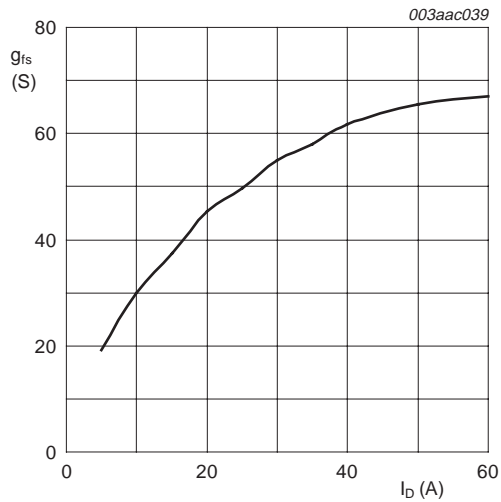
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



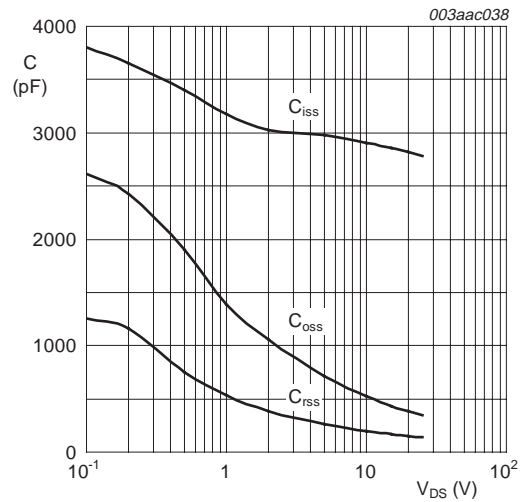
$T_j = 25 \text{ }^{\circ}C; V_{DS} = V_{GS}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



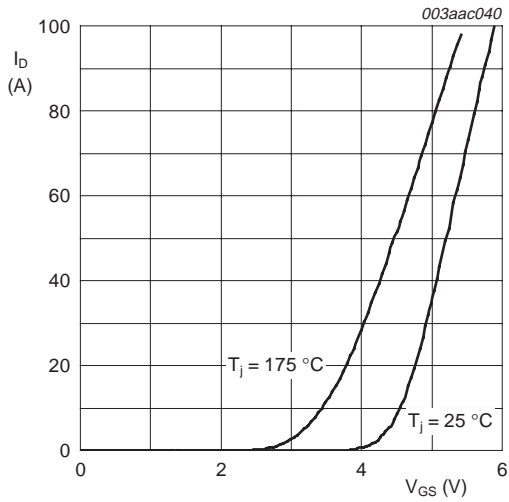
$T_j = 25 \text{ }^{\circ}C; V_{DS} = 25 \text{ V}$

Fig 11. Forward transconductance as a function of drain current; typical values



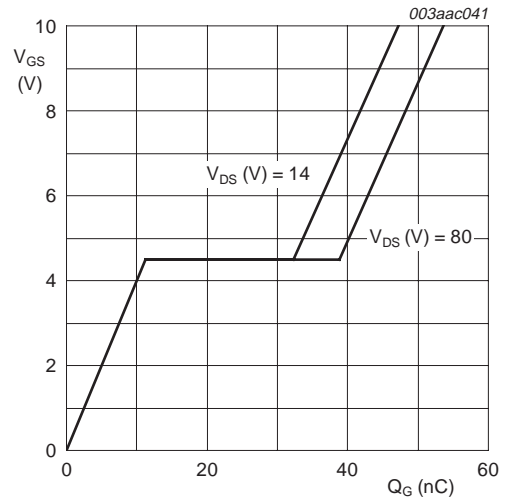
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



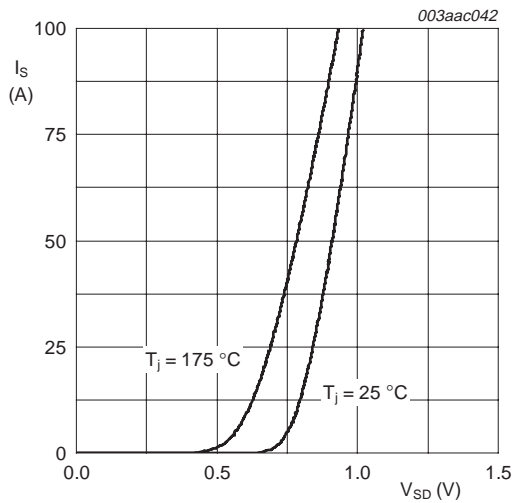
$V_{DS} = 25 \text{ V}$

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values



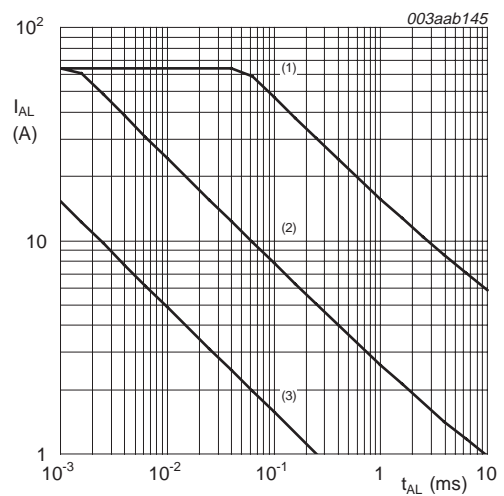
$T_j = 25 \text{ °C}; I_D = 25 \text{ A}$

Fig 14. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 \text{ V}$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values



See [Table note 1](#) of [Table 3](#) Limiting values.

- (1) Single-pulse; $T_j = 25 \text{ °C}$.
- (2) Single-pulse; $T_j = 125 \text{ °C}$.
- (3) Repetitive.

Fig 16. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

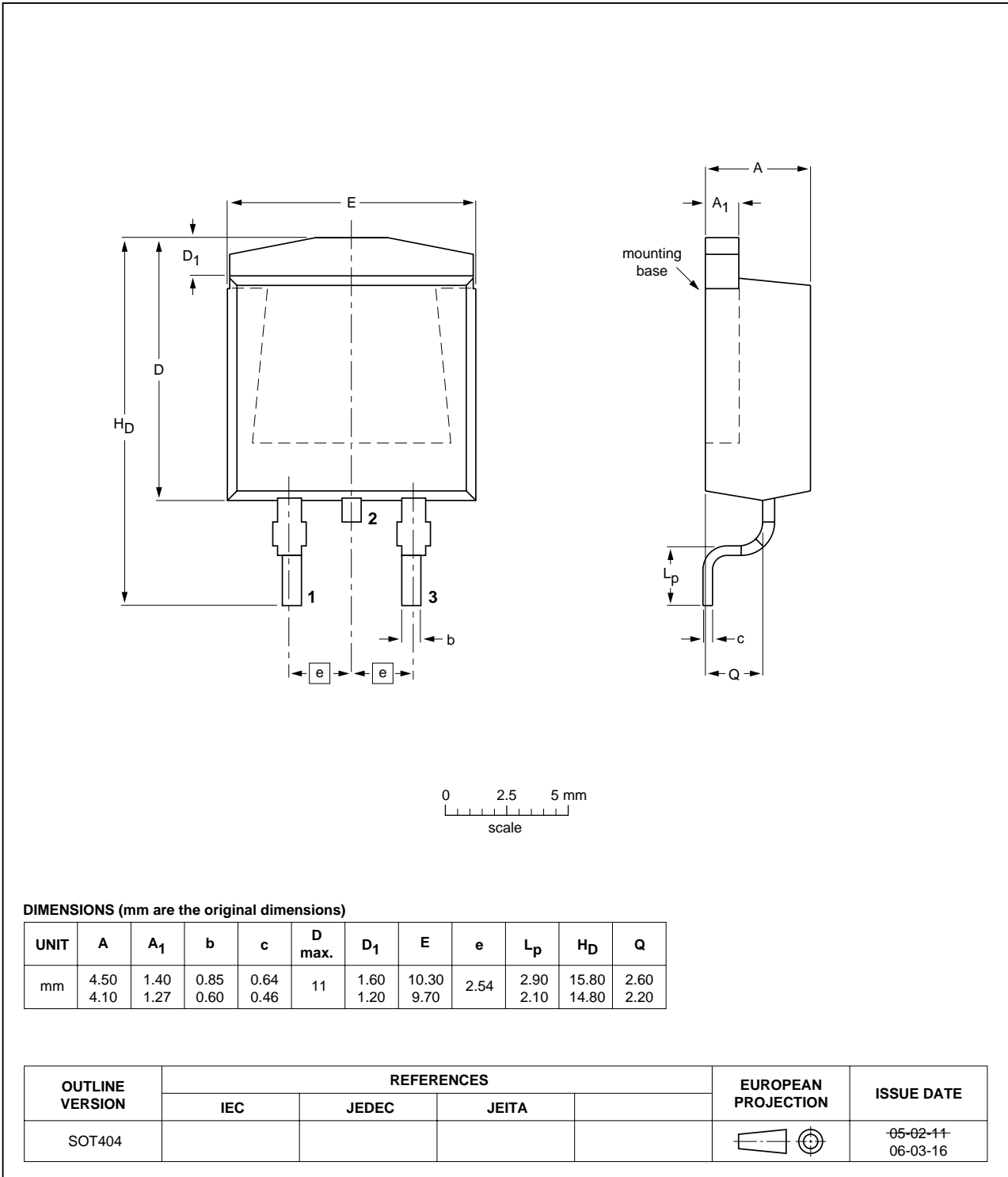
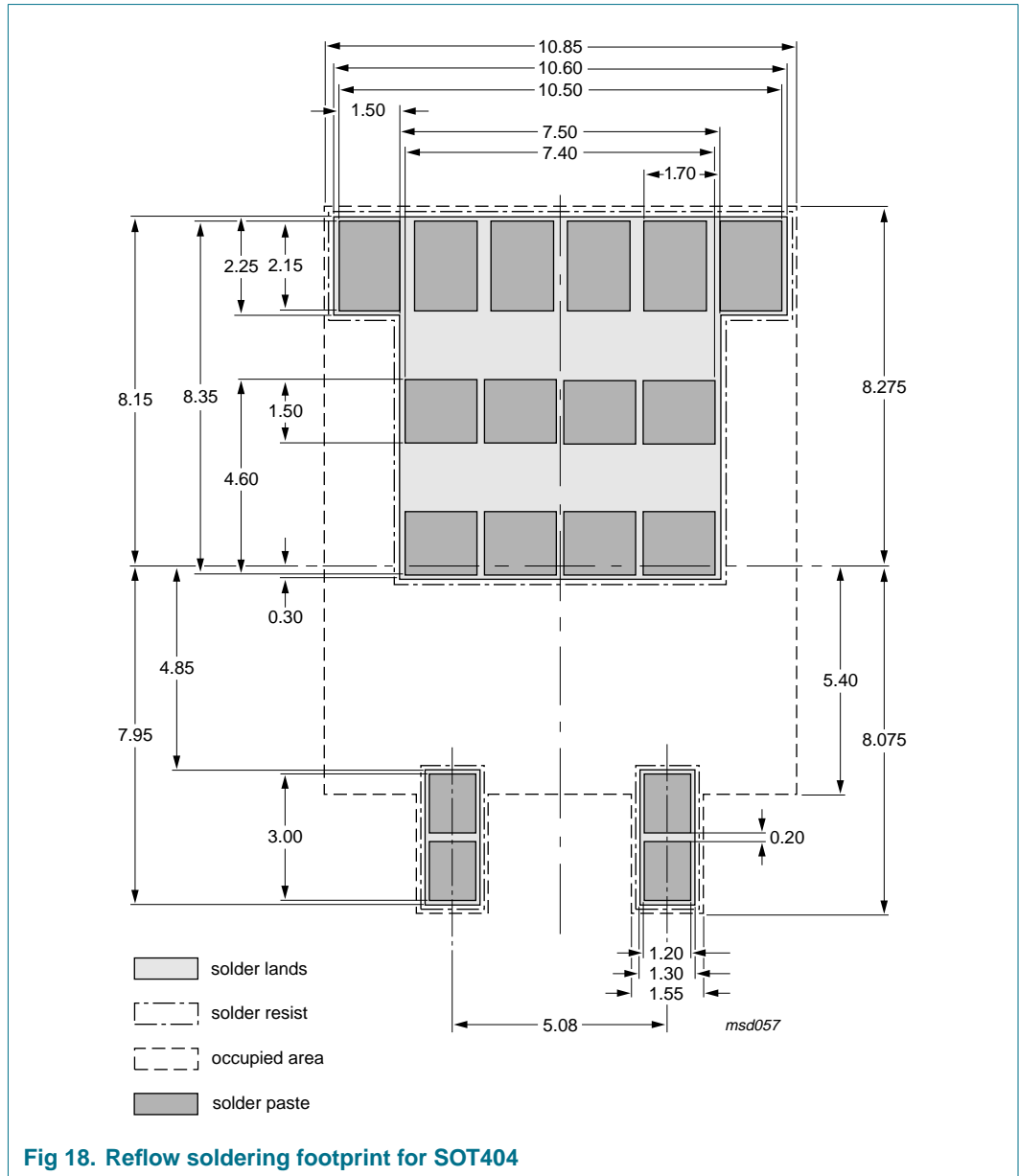


Fig 17. Package outline SOT404 (D2PAK)

8. Soldering



9. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7619-100B_1	20071010	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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